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John Borland¹, Seiichi Shishiguchi², Norihiko Matsuzaka², Masami Hane³, Masayasu Tanjo⁴, Peter Oesterlin⁵

¹J.O.B. Technologies, Aiea, HI

²Renesas Electronics Corp., Sagamihara, Japan

³Renesas Electronics America Inc., Albany, NY

⁴Nissin Ion Equipment Co. Ltd., Kyoto, Japan

⁵Jenoptik Innovavent, Gottingen, Germany

10:30AM-11:00AM

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Joseph F. Shepard Jr.¹, William A. Muth¹, Shawn MacNish²

¹IBM East Fishkill, NY

²KLA-Tencor, Hopewell Junction, NY

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Erik Rosseel¹, Claude Ortolland¹, Andriy Hikavyi¹, Tom Schram¹, Annelies Falepin², Thomas Hoffmann¹, Wilfried Vandervorst^{1,3}, Mike Ameen⁴, Lenny Rubin⁴

¹IMEC, Leuven, Belgium

²NXP semiconductors, Leuven, Belgium

³Instituut voor Kern- en Stralingsfysika, KU Leuven, Belgium

⁴Axcelis Technologies, Inc., Beverly, MA

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Erik Rosseel¹, Andriy Hikavyi¹, Jean-Luc Everaert¹, Liesbeth Witters¹, Jerome Mitard¹,
Thomas Hoffmann¹, Wilfried Vandervorst², A. Pap³, T. Pavelka³

¹IMEC, Leuven, Belgium

²Instituut voor Kern- en Stralingsfysika, KU Leuven, Leuven, Belgium

³Semilab Semiconductor Physics Laboratory, Co., Ltd., Budapest, Hungary

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Shaoyin Chen¹, Zhen Dai², Xiaoru Wang¹, Cam Lu¹, Michael Thompson², Yun Wang¹,
Jim McWherter¹

¹Ultratech, San Jose, CA

²Cornell University, Ithaca, NY

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Kouhei Tanaka¹, Yoshikazu Hashino¹, Masahiro Hashimoto¹, Hideki Yoshimi¹, Shinichi Sezaki¹,
Jason Reyes², Simon Prussin²

¹Nissin Ion Equipment Co., Ltd., 575 Kuze-Tonoshiro-Cho, Minami-Ku, Kyoto, Japan

²University of California Los Angeles, Los Angeles, CA

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Yonggen He¹, Bing Wu¹, Guobin Yu¹, Houguo Yang¹, Jin Lin¹, Seanf Zhang¹, Jiong-Ping Lu¹, JiYue Tang², Ganming Zhao²

¹Technology R&D center, Semiconductor Manufacturing International Corporation, Shanghai, PRC

²Applied Materials, Shanghai, PRC

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R. Beneyton¹, P. Morin¹, S. Muthukrishnan², D. Larmagnac³, A.J. Mayur², C. T. Richard¹

¹ST Microelectronics, Crolles, France

²Applied Materials, Sunnyvale, CA

³Applied Materials, Meylan, France

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¹Department of Electrical Engineering, University of California, Los Angeles, CA

²Nissin Ion Equipment Co., Kyoto, Japan

³Current Scientific, San Jose, CA

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Krishna Iyengar¹, Paulette Clancy², Michael Thompson³

¹School of Theoretical & Applied Mechanics, Cornell University, Ithaca, NY

²School of Chemical & Biomolecular Engineering, Cornell University, Ithaca, NY

³Department of Materials Science & Engineering, Cornell University, Ithaca, NY

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Rainer Paetzel¹, Jan Brune¹, Frank Simon¹, Ludolf Herbst¹, Masashi Machida², Junichi Shida²

¹Coherent, GmbH, Goettingen, Germany

²The Japan Steel Works, Yokohama, Japan

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J. Foerster, H. Vogt, A. Grabmaier

Institute of Electronic Components and Circuits, University of Duisburg-Essen, Duisburg, Germany

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United Microelectronics Corp., Sinshih Township, Taiwan

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United Microelectronics Corp., Sinshih Township, Taiwan

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E. Barbarini, S. Guastella, C. F. Pirri

Physics Department, Politecnico di Torino, Torino, Italy

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Robert Binder², Rainer Giedigkeit², Stephan Waidmann², Inka Richter², Kornelia Dittmar²,

Hartmut Prinz², Martin Weisheit²

¹ Ultratech Inc., San Jose, CA

² GlobalFoundries., Dresden, Germany

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¹Ultratech Inc., San Jose, CA

²Global Foundries Inc., Dresden, Germany

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¹DIMES, Delft University of Technology, Delft, The Netherlands

²ASML Netherlands B.V., Veldhoven, The Netherlands

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T. Seino¹, Y. Arai¹, N. Kobayashi¹, T. Kudo¹, K. Sano²

¹The Japan Steel Works, LTD., Laser & Plasma System Office, Kanagawa, Japan

²The Japan Steel Works, LTD., Laser & Plasma System Office, Tokyo, Japan

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Centrotherm Photovoltaics AG, Blaibern, Germany

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Peter Oesterlin¹, Ulrich Jager²

¹INNOVAVENT GmbH, Goettingen, Germany

²Fraunhofer Institute for Solar Energy Systems, Freiburg, Germany

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Applied Materials, Santa Clara, CA

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Andras Somogyi², Gyorgy Nadudvari², Lubek Jastrzebski³, Tibor Pavelka²

¹J.O.B. Technologies, Aiea, Hawaii

²Semilab, Budapest, Hungary

³Semilab SDI, Tampa, Florida

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T. Guarini, M. Bevan, M. Ripley, U. Ganguly¹, L. Date, H. Graoui, J. Swenberg
Applied Materials, Sunnyvale, CA

¹Dept of Electrical Engineering, Indian Institute of Technology Bombay, India

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Bo Lojek, Atmel Corporation, Colorado Springs, CO

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